L	Hits	Search Text	DB	Time stamp
Number				
1	1258464	polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/11/01 12:08
2	470779	epoxy (silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/11/01 12:20
3	80200	(polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsq osq)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:10
4	236569	(semiconductor silicon si gaas) with wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/11/01 12:10
5	15173	((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)) and ((semiconductor silicon si gaas) with wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:10
6	14402	(substrate carrier) and (((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)) and ((semiconductor silicon si gaas) with	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:11
7	13824	wafer)) ((integrated adj circuit) ic device chip die dice) and ((substrate carrier) and (((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)) and ((semiconductor silicon si gaas) with wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01
8	1510	dicing and ((substrate carrier) and (((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:22
9	1493	fsg osg)) and ((semiconductor silicon si gaas) with wafer))) dicing and (((integrated adj circuit) ic device chip die dice) and ((substrate carrier) and ((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)) and ((semiconductor silicon si gaas) with wafer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:14

	265661			0004/11/01
10	365661	(critical strain) with (strain energy release rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/11/01 14:37
11	213	(dicing and (((integrated adj circuit) ic device chip die dice) and ((substrate carrier) and (((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)) and ((semiconductor silicon si gaas) with wafer))))) and ((critical strain) with (strain energy release rate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:16
12	410378	(silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/11/01 12:21
13	213	(polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((dicing and ((integrated adj circuit) ic device chip die dice) and ((substrate carrier) and ((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate) epoxy) and ((silicon adj4 (nitride oxide dioxide carbon)) sin sic sio teos fteos fsg osg)) and ((semiconductor silicon si gaas) with wafer))))) and ((critical strain) with (strain energy release rate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01
14	14580	(polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:21
15	35388	(critical) with (strain energy release rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/11/01 12:33
	309	((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg)) and ((critical) with (strain energy release rate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:21

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17	16	dicing and (((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg)) and ((critical) with (strain energy release rate)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:22
18	55208	(critical strain) with (energy release rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/11/01 12:33
19	461	((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg)) and ((critical strain) with (energy release rate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:33
20	44	(((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg)) and ((critical strain) with (energy release rate))) and (dicing diced dice)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:34
21	30	((((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4 ether) (polyethylene adj4 terepthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg)) and ((critical strain) with (energy release rate))) and (dicing diced dice)) not (dicing and (((polyester phenolic polyimide polymide polysulfone (polyether adj4 either adh4 ketone) polyurethanes (polyarylene adj4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:46
		ether) (polyethylene adj4 terepthalate) epoxy) and ((semiconductor silicon si gaas) with wafer) and ((silicon adj4 (nitride oxide dioxide carbon)) sic sio teos fteos fsg osg)) and ((critical) with (strain energy release rate))))		
22	2061	257/780	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/11/01 12:46
23	848	257/790	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/11/01 12:46
24	1221	257/788	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/01 12:46

		1 050 (000		10004700
25	621	257/789	USPAT;	2004/11/01
			US-PGPUB;	12:46
			EPO; JPO;	!
			DERWENT;	
			IBM TDB	
26	2228	257/790 257/788 257/789	USPAT;	2004/11/01
			US-PGPUB;	12:46
			EPO; JPO;	
	}		DERWENT;	
}			IBM TDB	
27	280	(257/790 257/788 257/789) and (polyester	USPAT;	2004/11/01
1 - '	200	phenolic polyimide polymide polysulfone	US-PGPUB;	12:47
1	1	(polyether adj4 either adh4 ketone)	1	12.47
			EPO; JPO;	
1		polyurethanes (polyarylene adj4 ether)	DERWENT;	
		(polyethylene adj4 terepthalate) epoxy)	IBM_TDB	
		and ((silicon adj4 (nitride oxide dioxide		
		carbon)) sin sic sio teos fteos fsg osg)		
28	110	, ,	USPAT;	2004/11/01
		(polyester phenolic polyimide polymide	US-PGPUB;	14:35
1		polysulfone (polyether adj4 either adh4 -	EPO; JPO;	
		ketone) polyurethanes (polyarylene adj4	DERWENT;	1
		ether) (polyethylene adj4 terepthalate)	IBM TDB	1
		epoxy) and ((silicon adi4 (nitride oxide	_]
		dioxide carbon)) sin sic sio teos fteos		
		fsg osg)) and wafer		
29	1372	polyarylene adj ether	USPAT;	2004/11/01
	15/2	poryaryrene adj ether	US-PGPUB;	14:36
			,	14.36
			EPO; JPO;	
			DERWENT;	
20	1 400	//military - 14 / /military 1 - 1 - 1 - 1 - 1	IBM_TDB	
30	428	, , ,	USPAT;	2004/11/01
	l	carbon)) sin sic sio teos fteos fsg osg)	US-PGPUB;	14:37
		and (polyarylene adj ether)	EPO; JPO;	
			DERWENT;	į l
			IBM_TDB	
31	19	((critical strain) with (strain energy	USPĀT;	2004/11/01
		release rate)) and (((silicon adj4	US-PGPUB;	14:37
		(nitride oxide dioxide carbon)) sin sic	EPO; JPO;	
		sio teos fteos fsg osg) and (polyarylene	DERWENT;	
		adj ether))	IBM TDB	
L	l	[T T T T T T T T T T T T T T T T T T T	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	